SWITCHMODE™ Power Rectifier 45 V, 30 A

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 150°C Operating Junction Temperature
- 30 A Total (15 A Per Diode Leg)
- Guard-Ring for Stress Protection

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped 50 Units Per Plastic Tube
- This is a Pb-Free Device*

MAXIMUM RATINGS

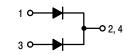
Please See the Table on the Following Page



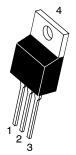
ON Semiconductor®

http://onsemi.com

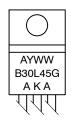
DUAL SCHOTTKY BARRIER RECTIFIERS 30 AMPERES, 45 VOLTS



MARKING DIAGRAMS



TO-220 CASE 221A PLASTIC





TO-220 CASE 221D STYLE 3



B30L45 = Device Code A = Assembly Location

Y = Year
WW = Work Week
AKA = Polarity Designator
G = Pb-Free Device

ORDERING INFORMATION

Device	Package	Shipping
MBR30L45CTG	TO-220 (Pb-Free)	50 Units/Rail
MBRF30L45CTG	TO-220FP (Pb-Free)	50 Units/Rail

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS (Per Diode Leg)

Rating		Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	45	V
Average Rectified Forward Current (Rated V_R) $T_C = 137^{\circ}C$	I _{F(AV)}	15	Α
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz)	I _{FRM}	30	Α
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	190	Α
Operating Junction Temperature (Note 1)	TJ	-55 to +150	°C
Storage Temperature	T _{stg}	- 55 to +175	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V
HERMAL CHARACTERISTICS		•	
Junction-t	n-to-Case $R_{ heta JC}$ o-Ambient $R_{ heta JA}$ $R_{ heta JC}$	1.9 45 2.2	°C/W
ELECTRICAL CHARACTERISTICS (Per Diode Leg)			
Maximum Instantaneous Forward Voltage (Note 2) $ \begin{aligned} &(I_F=15~A,T_C=25^\circ\text{C})\\ &(I_F=15~A,T_C=125^\circ\text{C})\\ &(I_F=30~A,T_C=25^\circ\text{C})\\ &(I_F=30~A,T_C=125^\circ\text{C}) \end{aligned} $	VF	0.50 0.44 0.61 0.60	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 25^{\circ}C$) (Rated DC Voltage, $T_C = 125^{\circ}C$)	i _R	0.65 250	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.
- 2. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

TYPICAL CHARACTERISTICS

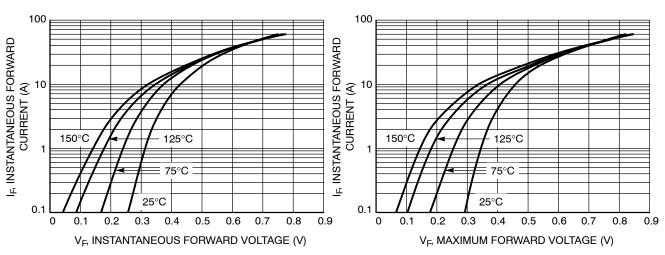


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

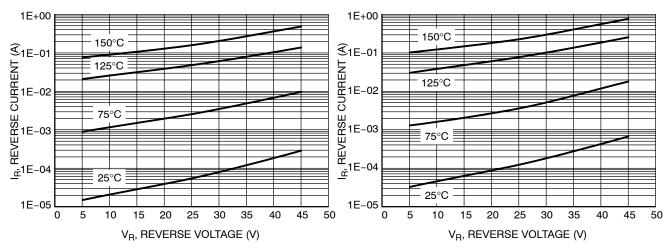


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current

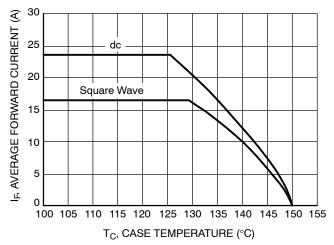


Figure 5. Current Derating

TYPICAL CHARACTERISTICS

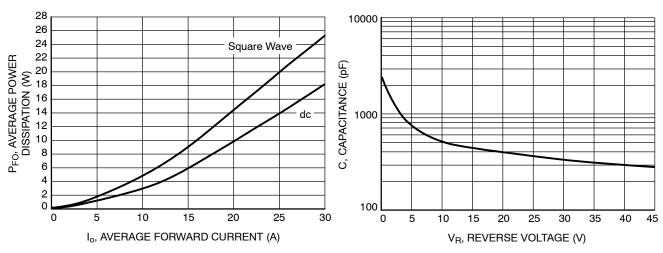


Figure 6. Forward Power Dissipation

Figure 7. Typical Capacitance

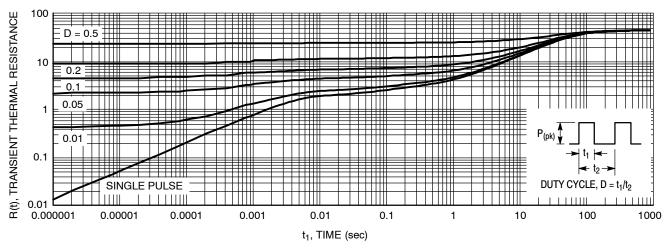


Figure 8. Thermal Response Junction-to-Ambient for MBR30L45CTG

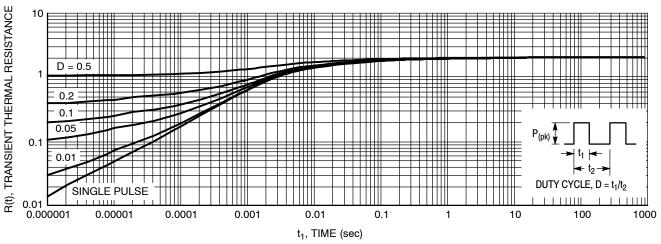


Figure 9. Thermal Response Junction-to-Case for MBR30L45CTG

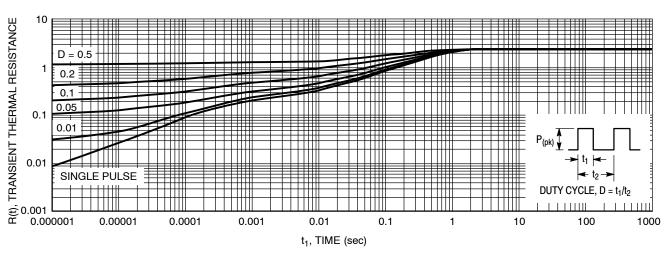
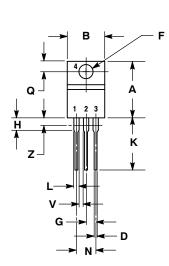
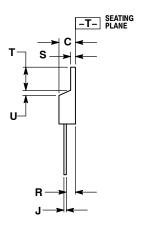


Figure 10. Thermal Response Junction-to-Case for MBRF30L45CTG

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AF**



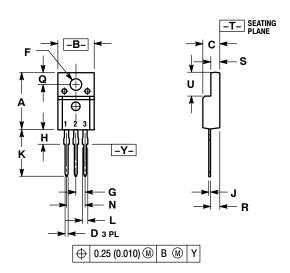


- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

TO-220 FULLPAK

CASE 221D-03 **ISSUE K**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH
- 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

	INCHES		MILLIN	MILLIMETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.617	0.635	15.67	16.12	
В	0.392	0.419	9.96	10.63	
С	0.177	0.193	4.50	4.90	
D	0.024	0.039	0.60	1.00	
F	0.116	0.129	2.95	3.28	
G	0.100 BSC		2.54 BSC		
Н	0.118	0.135	3.00	3.43	
J	0.018	0.025	0.45	0.63	
K	0.503	0.541	12.78	13.73	
L	0.048	0.058	1.23	1.47	
N	0.200 BSC		5.08 BSC		
Q	0.122	0.138	3.10	3.50	
R	0.099	0.117	2.51	2.96	
S	0.092	0.113	2.34	2.87	
U	0.239	0.271	6.06	6.88	

STYLE 3:

PIN 1. ANODE

CATHODE 3. ANODE

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